

#### 40V N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI3333-8

### **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>C</sub> = +25°C
	20mΩ @ V <sub>GS</sub> = 10V	21.2A
40V	25mΩ @ V <sub>GS</sub> = 4.5V	19.1A

### **Description and Applications**

This MOSFET is designed to minimize the on-state resistance (R<sub>DS(ON)</sub>) yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Wireless Charging
- DC-DC Converters
- Power Management

### **Features and Benefits**

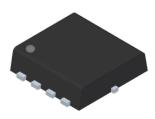
- 100% Unclamped Inductive Switching (UIS) Test in Production Ensures More Reliable and Robust End Application
- Low R<sub>DS(ON)</sub> Ensures On-State Losses Are Minimized
- Low On-Resistance
- Low Input Capacitance
- · Fast Switching Speed
- Low Input/Output Leakage
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. https://www.diodes.com/quality/product-definitions/

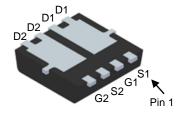
### **Mechanical Data**

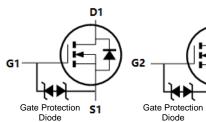
- Case: PowerDI<sup>®</sup>3333-8
- Case Material: Molded Plastic, "Green" Molding Compound.
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
   Solderable per MIL-STD-202, Method 208 (2)
- Weight: 0.072 grams (Approximate)

#### PowerDI3333-8 (Type UXC)









Top View

**Bottom View** 

Internal Schematic

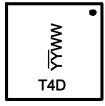
### Ordering Information (Note 4)

Part Number	Case	Packaging
DMT4015LDV-7	PowerDI3333-8 (Type UXC)	2,000/Tape & Reel
DMT4015LDV-13	PowerDI3333-8 (Type UXC)	3,000/Tape & Reel

Notes:

- $1.\ No\ purposely\ added\ lead.\ Fully\ EU\ Directive\ 2002/95/EC\ (RoHS),\ 2011/65/EU\ (RoHS\ 2)\ \&\ 2015/863/EU\ (RoHS\ 3)\ compliant.$
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

### Marking Information



 $\frac{\text{T4D}}{\text{YY}}$  = Product Type Marking Code  $\frac{\text{YYW}}{\text{YY}}$  = Date Code Marking  $\frac{\text{YY}}{\text{YY}}$  = Last Two Digits of Year (ex: 20 = 2020) WW = Week Code (01 to 53)

D2



# **Maximum Ratings** (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage	V <sub>DSS</sub>	40	V		
Gate-Source Voltage	Vgss	±16	V		
Continuous Drain Current (Note 6) $V_{GS} = 10V$ $T_{C} = +25^{\circ}$ $T_{C} = +70^{\circ}$			ΙD	21.2 17.0	А
Continuous Drain Current (Note 6) V <sub>GS</sub> = 10V	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	lp	7.8 6.3	А	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I <sub>DM</sub>	50	Α		
Maximum Continuous Body Diode Forward Current (Note 6)			Is	2	Α
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)			Ism	50	Α
Avalanche Current, L = 0.1mH			las	20.7	Α
Avalanche Energy, L = 0.1mH			Eas	21.4	mJ

## Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T <sub>A</sub> = +25°C	PD	1.1	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	110.6	°C/W
Total Power Dissipation (Note 6)	T <sub>A</sub> = +25°C	PD	2.0	W
Thermal Resistance, Junction to Ambient (Note 6)  Steady State		R <sub>θ</sub> JA	61.2	°C/W
Thermal Resistance, Junction to Case (Note 6)	R <sub>θ</sub> JC	8.3	°C/W	
Operating and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

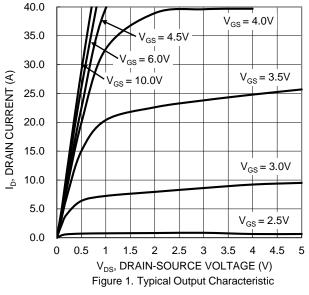
# **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

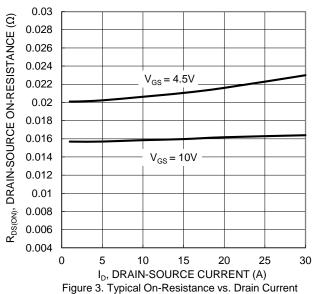
Characteristic	Cymphol	Min	Turn	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)	Symbol	IVIII	Тур	IVIAX	Unit	rest Condition	
, ,	DV	40	l	_	V	\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\	
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>				-	$V_{GS} = 0V, I_D = 1mA$	
Zero Gate Voltage Drain Current	IDSS		_	1	μA	$V_{DS} = 40V$ , $V_{GS} = 0V$	
Gate-Source Leakage	Igss	_	_	±10	μΑ	$V_{GS} = \pm 16V$ , $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	Vgs(TH)	0.75	_	2.5	V	$V_{DS} = V_{GS}$ , $I_D = 250\mu A$	
Static Drain-Source On-Resistance	Descent		15.3	20	mΩ	$V_{GS} = 10V, I_D = 8A$	
Static Drain-Source On-Resistance	Rds(on)	_	20.1	25	11122	$V_{GS} = 4.5V, I_{D} = 4A$	
Diode Forward Voltage	Vsp	_	0.7	1.2	V	V <sub>G</sub> S = 0V, I <sub>S</sub> = 1A	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	Ciss	_	808		рF	V 20V V 0V	
Output Capacitance	Coss	_	279	_	рF	V <sub>DS</sub> = 30V, V <sub>GS</sub> = 0V, - f = 1MHz	
Reverse Transfer Capacitance	Crss	_	30		рF	1 = 11/1112	
Gate Resistance	Rg	_	1.4	_	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Qg	_	8.6	_	nC		
Total Gate Charge (VGS = 10V)	Qg		15.7		nC	V <sub>DS</sub> = 30V. I <sub>D</sub> = 10A	
Gate-Source Charge	Qgs	_	2.9		nC	VDS = 30V, ID = TOA	
Gate-Drain Charge	Qgd	_	3.4	_	nC	7	
Turn-On Delay Time	td(ON)	_	7.5		ns		
Turn-On Rise Time	t <sub>R</sub>	_	2.7	_	ns	V <sub>G</sub> S = 10V, V <sub>D</sub> S = 30V,	
Turn-Off Delay Time	tD(OFF)	_	17.4	_	ns	$R_g = 6\Omega$ , $I_D = 10A$	
Turn-Off Fall Time	t <sub>F</sub>	_	8.9	_	ns	]	
Body Diode Reverse Recovery Time	trr	_	26.7	_	ns	1 404 11/11 4004/	
Body Diode Reverse Recovery Charge	Q <sub>RR</sub>	_	16.2	_	nC	$I_F = 10A$ , di/dt = 100A/ $\mu$ s	

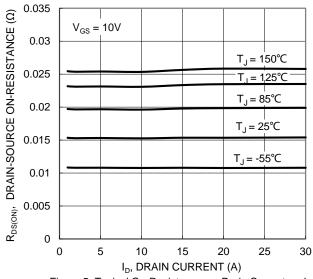
Notes:  $\,$  5. Device mounted on FR-4 PCB, with minimum recommended pad layout, single sided.

- 6. Device mounted on FR-4 substrate PCB, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
- 7. Short duration pulse test used to minimize self-heating effect.
- 8. Guaranteed by design. Not subject to product testing.









and Gate Voltage

Figure 5. Typical On-Resistance vs. Drain Current and Temperature

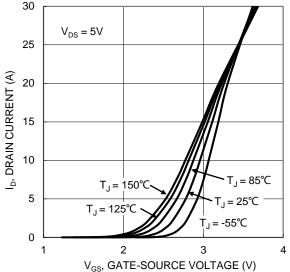
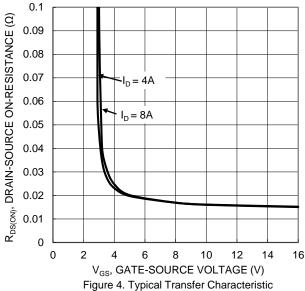


Figure 2. Typical Transfer Characteristic



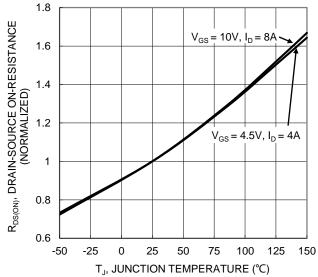


Figure 6. On-Resistance Variation with Temperature



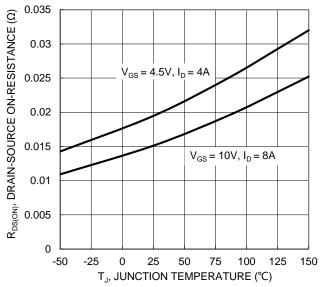


Figure 7. On-Resistance Variation with Temperature

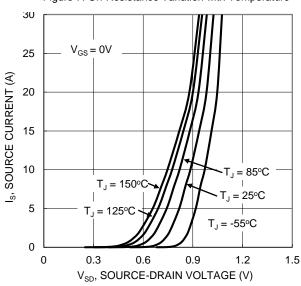


Figure 9. Diode Forward Voltage vs. Current

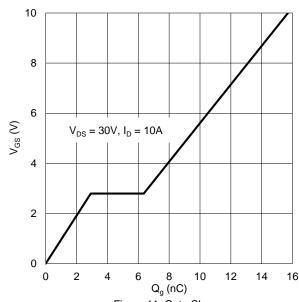
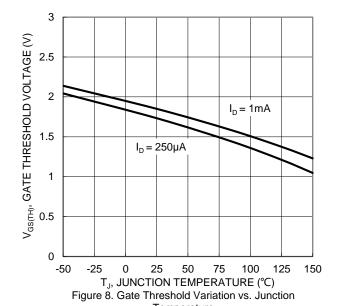
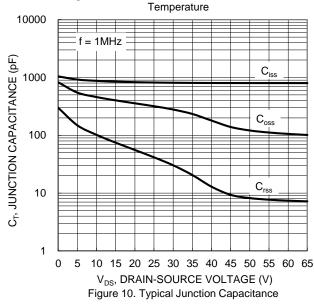
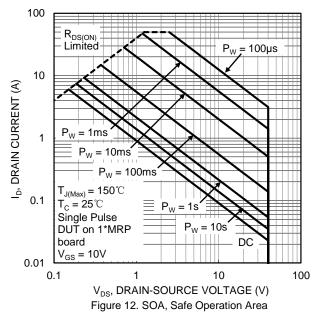


Figure 11. Gate Charge









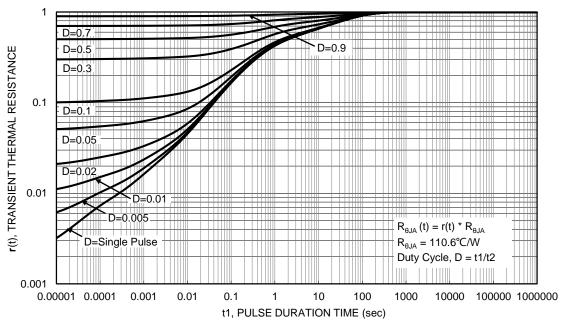


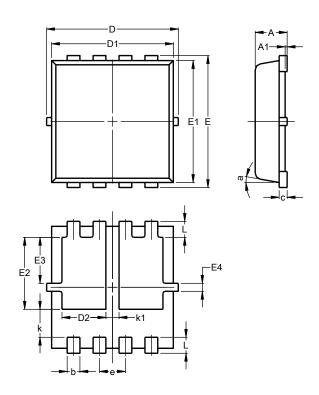
Figure 13. Transient Thermal Resistance



## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### PowerDI3333-8 (Type UXC)

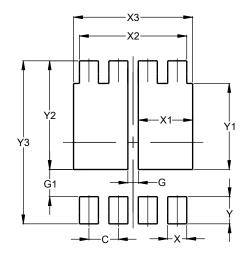


PowerDI3333-8						
(Type UXC) Dim   Min   Max   Typ						
Dim	Min	Тур				
Α	0.75	0.85	0.80			
Α1	0.00	0.05				
b	0.25	0.40	0.32			
С	0.10	0.25	0.15			
D	3.20	3.40	3.30			
D1	2.95	3.15	3.05			
D2	0.90	1.30	1.10			
Е	3.20	3.40	3.30			
E1	2.95	3.15	3.05			
E2	1.60	2.00	1.80			
E3	0.95	1.35	1.15			
E4	0.10	0.30	0.20			
е	_	-	0.65			
L	0.30	0.50	0.40			
k	0.50	0.90	0.70			
k1	0.13	0.53	0.33			
а	0°	12°	10°			
All Dimensions in mm						

## **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### PowerDI3333-8 (Type UXC)



Dimensions	Value (in mm)		
С	0.650		
G	0.230		
G1	0.600		
Х	0.420		
X1	1.200		
X2	2.370		
Х3	2.630		
Υ	0.600		
Y1	1.900		
Y2	2.400		
Y3	3.600		



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